

REMARKS

The Examiner is thanked for the thorough review and consideration of the present application. The final Office Action dated October 10, 2003 has been received and its contents carefully reviewed.

By this Response, Applicants have amended claim 1 to clarify the subject matter recited in the claim. No new matter has been added. Applicants kindly acknowledge the allowance of claims 3-5 and 21-22. Claims 1-5, 21 and 22 are pending in the application. Reconsideration and withdrawal of the rejection based upon the above amendment and the following remarks are requested.

In the Office Action, claims 1 and 2 are rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,163,356 issued to Song et al. (hereafter "Song"). Applicants respectfully traverse the rejection because Song fails to teach or suggest each of the features recited in the claims of the present application. In particular, Song fails to teach or suggest a liquid crystal display device that includes, among other features, "a gate pad electrode at one end of the gate line, wherein the gate pad electrode is formed of a same material and in a same layer as the pixel electrode in a single layer in direct contact over the first insulating layer, and wherein the gate pad electrode electrically contacts the exposed portion of the gate line and overlaps the first insulating layer", as recited in independent claim 1.

On pages 3 and 5 of the Office Action, the Examiner appears to equate the dummy gate pad (115b) of Song to the gate pad electrode 108 of the present application, and the gate pad (115) to the gate pad 104 of the present application. However, Applicants respectfully submit using this rational would result in the dummy gate pad (115) of Song failing to electrically contact the exposed portion of the gate line, as required in claim 1 of the present application. Also, in Song, the dummy gate pad 115b is "made of the semiconductor layer 133 and the impurity doped semiconductor layer 135 (Col. 8, lines 37-39). Later, the impurity doped semiconductor is etched away and the "dummy gate pad 115b contains only the semiconductor layer 133 made of intrinsic semiconductor material" (Col. 8, lines 62-64). Whereas, "a transparent conductive material such as ITO (indium tin oxide) is deposited on the protective layer 137 and patterned to form a pixel electrode 141" (Col. 9, lines 23-26). In claim 1 of the

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present application, the "the gate pad electrode is formed of a same material and in the same layer as the pixel electrode". Thus, Song fails to teach each of the features recited in claim 1.

Further, as illustrated in FIG. 7E in the present application, the gate pad electrode 108 is formed of a single layer in direct contact over the first insulating layer 150, and the gate pad electrode 108 electrically contacts the exposed portion of the gate line. Whereas, as depicted in FIG. 8F of Song, the gate pad connecting terminal 157 contacts the gate pad 115; however, the gate pad connecting terminal 157 is not in direct contact over the first insulating layer 117. Because Song fails to teach or suggest each of the features recited in claim 1 and its rejected dependent claim 2, claims 1 and 2 are patentable over Song. Reconsideration and withdrawal of the rejection are requested.

In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to pass this application to issue. If the Examiner deems that a telephone conversation would further the prosecution of this application, the Examiner is invited to call the undersigned at (202) 496-7500.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: January 12, 2004

Respectfully submitted,

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